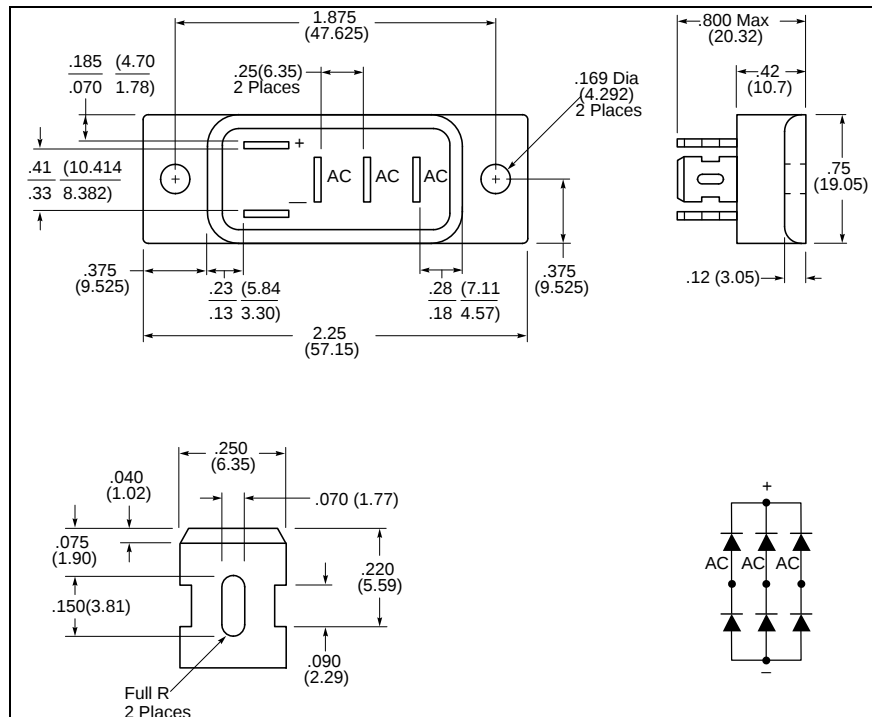


TECHNICAL DATA
DATA SHEET 260, REV D**THREE PHASE FULL WAVE
BRIDGE RECTIFIER ASSEMBLY****DESCRIPTION: 600 VOLT, 15 AMP, 195 NANOSECOND THREE PHASE BRIDGE RECTIFIER ASSEMBLY.****MAX. RATINGS / ELECTRICAL CHARACTERISTICS** All ratings are at $T_A = 25^\circ\text{C}$ unless otherwise specified.

RATING	CONDITIONS	MIN	TYP	MAX	UNIT
Peak Inverse Voltage (PIV)	S25A360FR S25A340FR	-	-	600 400	Vdc
Average DC Output Current ($T_C = \text{Case Temp}$) (I_o)	$T_C = 55^\circ\text{C}$ $T_C = 100^\circ\text{C}$ $T_C = 125^\circ\text{C}$	-	-	15 11 7.5	Amps
Average DC Output Current Ambient Temp. (no heat sink) (I_o)	$T_A = 25^\circ\text{C}$ $T_A = 55^\circ\text{C}$ $T_A = 100^\circ\text{C}$	-	-	5.0 4.0 2.5	Amps
Peak Single Cycle Surge Current (I_{FSM})	$t_p = 8.3 \text{ ms}$, Single Half Cycle Sine Wave, Superimposed on Rated Load	-	-	100	Amps(pk)
Peak Recurring Surge Current (I_{FRM})	$T_A = 25^\circ\text{C}$	-	-	40	Amps
Operating and Storage Temp. (T_{op} & T_{stg})	-	-55	-	+150	$^\circ\text{C}$
Maximum Forward Voltage (V_f)	$I_f = 9\text{A}$ (300 μsec pulse, duty cycle < 2%)	-	-	1.6	Volts
Maximum Instantaneous Reverse Current At Rated (PIV)	$T_A = 25^\circ\text{C}$ $T_A = 100^\circ\text{C}$	-	-	5.0 100	μAmps
Reverse Recovery Time (t_{rr})	$I_f = 0.5\text{A}$, $I_r = 1.0\text{A}$, $I_{rr} = 0.25\text{A}$	-	-	195	nsec
Thermal Resistance (θ_{JL})	-	-	-	1.5	$^\circ\text{C/W}$

TECHNICAL DATA
DATA SHEET 260, REV D

MECHANICAL DIMENSIONS: In Inches / mm



Note: Case finish - Black Anodized

FIG. 404

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